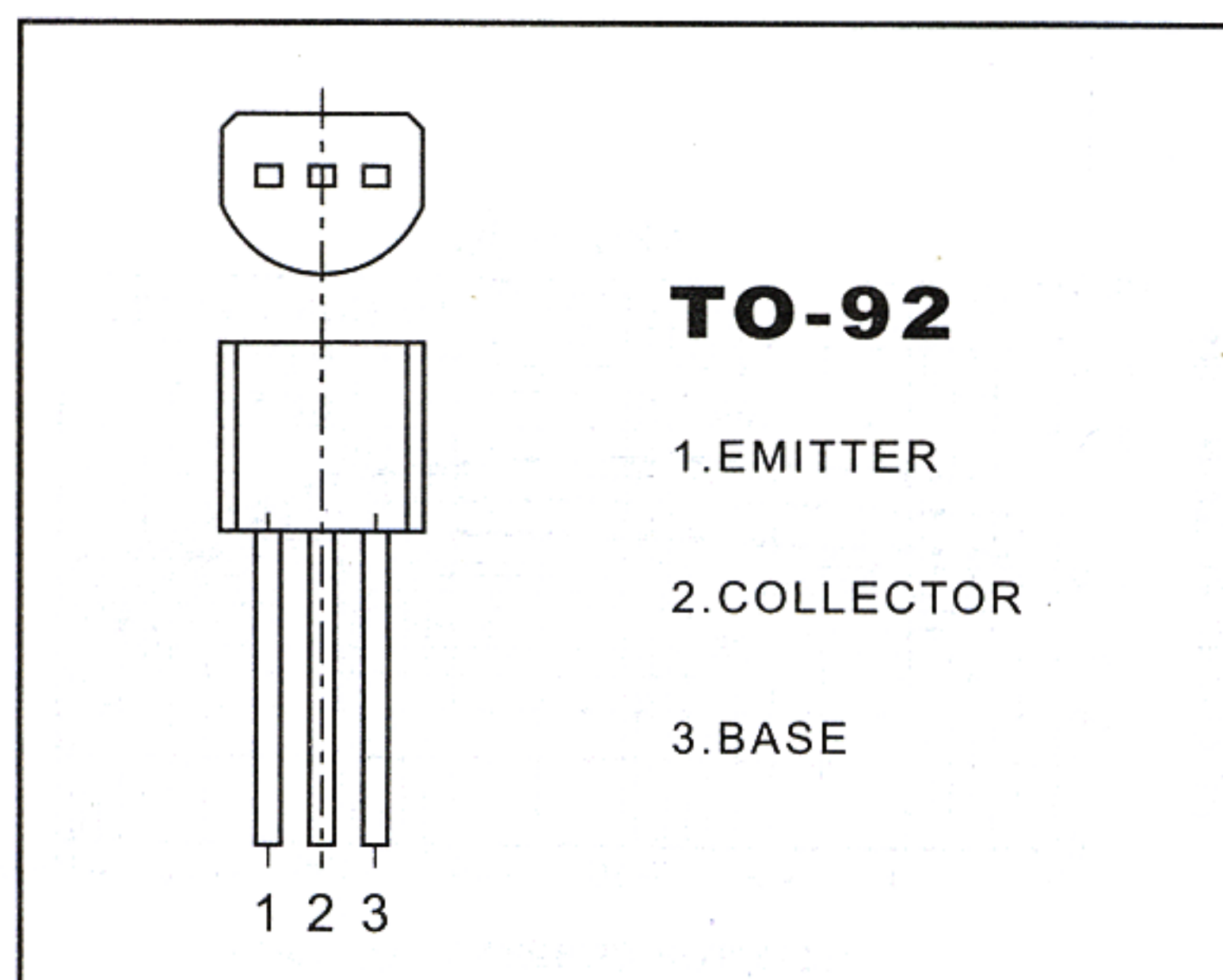


## 2SA562 TRANSISTOR(NPN)



### FEATURES

#### Power dissipation

$P_{CM}$ : 0.5W ( $T_{amb}=25^{\circ}C$ )

#### Collector current

$I_{CM}$ : -0.5 A

#### Collector-base voltage

$V_{(BR)CBO}$ : -35 V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### ELECTRICAL CHARACTERISTICS

( $T_{amb}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -35 V, I_E = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5 V, I_C = 0$		-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -1 V, I_C = -100 mA$	70	240	
	$h_{FE(2)}$	$V_{CE} = -6 V, I_C = -400 mA$	25		
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = -100 mA, I_B = -10 mA$		-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -1 V, I_C = -100 mA$		-1	V
Transition frequency	$f_T$	$V_{CE} = -6 V, I_C = -20 mA$	200		MHz
		$f = 30MHz$			

### CLASSIFICATION OF $h_{FE(1)}$

Rank		O	Y
Range	$h_{FE(1)}$	70-140	120-240
	$h_{FE(2)}$	25min	40min



